GP1M003A080H

GP1M003A080H Information

For Reference Only

Part Number GP1M003A080H
Manufacturer Global Power Technologies Group
Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single
Description MOSFET N-CH 800V 3A TO220
Package TO-220-3

For the pricing/inventory/lead time, please contact us
Website: https://www.heisener.com
E-mail: salesdept@heisener.com

Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.

GP1M003A080H Specifications

Manufacturer Part Number	GP1M003A080H
Manufacturer	Global Power Technologies Group
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-220-3
Series	-
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	800V
Current - Continuous Drain (Id) @ 25°C	3A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs(th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	19nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	696pF @ 25V
Vgs (Max)	±30V
FET Feature	-
Power Dissipation (Max)	94W (Tc)
Rds On (Max) @ Id, Vgs	4.2 Ohm @ 1.5A, 10V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Through Hole
Supplier Device Package	TO-220
Package / Case	TO-220-3
	Report errors?

GP1M003A080H Guarantees

Quality Guarantees
We provide 90 days warranty. *
If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

Service Guarantees
We guarantee 100% customer satisfaction.
Our experienced sales team and tech support team back our services to satisfy all our customers.

GP1M003A080H Payment Methods

GP1M003A080H Shipping Methods

If you have any question about GP1M003A080H, please do not hesitate to contact us!
Website: https://www.heisener.com
E-mail: salesdept@heisener.com